



Ruttonsha International Rectifier Ltd.

SILICON CONTROLLED RECTIFIERS

**High Power Thyristor
Hockey Puk Version
K-PUK Series 2500PK**

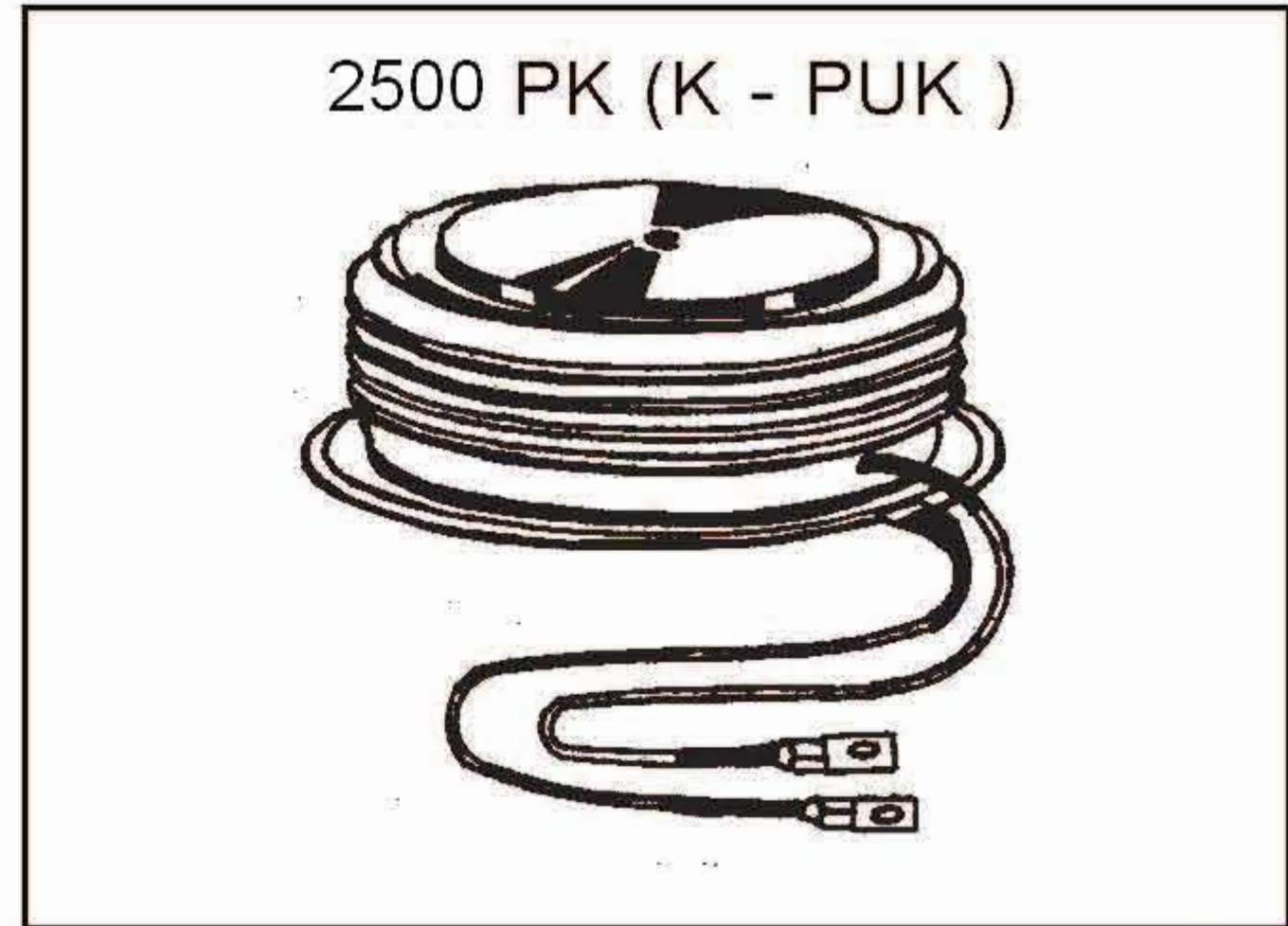
Types : 2500PK 20 to 2500PK 80

FEATURES

- € Center amplifying gate.
- € Metal case with ceramic insulator
- € International standard case A-24.
- € High profile hockey - puk.

TYPICAL APPLICATIONS

- € DC motor control (e.g. for machine tools).
- € Controlled rectifiers (e.g. for battery charging, Uninterrupted Power Supply).
- € AC controllers (e.g. for temperature control, lights control).



MAJOR RATINGS & CHARACTERISTICS

Parameters	2500PK	Units	
$I_{T(AV)}$	2500	A	
@ T_{hs}	55	$^{\circ}C$	
$I_{T(RMS)}$	3925	A	
@ T_{hs}	55	$^{\circ}C$	
I_{TSM}	@ 50 Hz	42500	A
I^2t	@ 50 Hz	9031	KA ² s
V_{DRM} / V_{RRM}	200 to 800	V	
t_q	typical	200	μs
T_J	-40 to 125	$^{\circ}C$	

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2500PK..Series

ON-STATE CONDUCTION

Type Number	Voltage Code	V_{RRM} / V_{DRM} , max. repetitive peak and off-state voltage V	V_{RSM} , max. non-repetitive peak voltage V	I_{DRM} / I_{RRM} max. @ 125°C mA
2500PK	20	200	300	100
	40	400	500	
	60	600	700	
	80	800	900	

ON-STATE CONDUCTION

	Parameter	2500PK	Units	Conditions
$I_{T(AV)}$	Max. average on-state current @ heat sink temperature	2500	A	180° conduction, half sine wave double side cooled
		55	°C	
$I_{T(RMS)}$	Max. RMS on-state current	3925		@55°C heat sink temperature (double side cooled)
I_{TSM}	Max. peak one cycle non-repetitive surge current	42500	A	t = 10ms Sinusoidal half wave, Initial $T_J = T_J$ max.
I^2t	Maximum I^2t for fusing	9031	kA ² s	t = 10ms
$I^2\sqrt{t}$	Maximum $I^2\sqrt{t}$ for fusing	90310	kA ² √s	t = 0.1 to 10ms.
$V_{T(TO)}$	Threshold voltage	0.83	V	$T_J = T_J$ max.
r_t	On state slope resistance	0.08	mΩ	$T_J = T_J$ max.
V_{TM}	Max. on state voltage	1.25	V	$I_{pk} = 4000$ A, $T_J = T_J$ max., $t_p = 10$ ms sine pulse
I_H	Maximum holding current	600	mA	$T_J = 25$ °C, anode supply 12V resistive load
I_L	Maximum Latching current	1000		

SWITCHING

	Parameter	2500PK	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	100	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1$ μs $T_J = T_J$ max., anode voltage $\leq 80\% V_{DRM}$
t_d	Typical delay time	1.9	μs	Gate current 1A, $di_g/dt = 1$ A/μs $V_d = 0.67\% V_{DRM}$, $T_J = 25$ °C
t_q	Typical turn-off time	200		$I_{TM} = 550$ A, $T_J = T_J$ max., $di/dt = 40$ A/μs, $V_R = 50$ V $dv/dt = 20$ V/μs, Gate 0V 100Ω, $t_p = 500$ μs

SILICON CONTROLLED RECTIFIERS

2200PK..Series

BLOCKING

	Parameter	2500PK	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_{J \text{ max.}}$, linear to 80% rated V_{DRM}
I_{RRM} I_{DRM}	Max. peak reverse and off-state leakage current	100	mA	$T_J = T_{J \text{ max.}}$, rated V_{DRM} / V_{RRM} applied

*Higher dv/dt is available on request

TRIGGERING

	Parameter	2500PK		Units	Conditions
P_{GM}	Maximum peak gate power	16.0		W	$T_J = T_{J \text{ max.}}$, $t_p \leq 5\text{ms}$
$P_{\text{G(AV)}}$	Maximum average gate power	3.0			$T_J = T_{J \text{ max.}}$, $f = 50\text{Hz}$, $d\% = 50$
I_{GM}	Max. peak positive gate current	3.0		A	$T_J = T_{J \text{ max.}}$, $t_p \leq 5\text{ms}$
$+V_{\text{GM}}$	Max. peak positive gate voltage	20		V	$T_J = T_{J \text{ max.}}$, $t_p \leq 5\text{ms}$
$-V_{\text{GM}}$	Max. peak negative gate voltage	5.0			
I_{GT}	DC gate current required to trigger	TYP.	MAX.	mA	$T_J = 25^\circ\text{C}$ Max. required gate trigger/current / voltage are the lowest value which will trigger all units 12V anode-to-cathode applied.
		100	250		
V_{GT}	DC gate voltage required to trigger	1.1	3.0	V	$T_J = 25^\circ\text{C}$
I_{GD}	DC gate current not to trigger	10		mA	$T_J = T_{J \text{ max.}}$ Max. gate current / voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied.
V_{GD}	DC gate voltage not to trigger	0.25		V	

THERMAL AND MECHANICAL SPECIFICATION

	Parameter	2500PK	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	$^\circ\text{C}$	
T_{stg}	Max. storage temperature range	-40 to 150		
$R_{\text{thJ-hs}}$	Max. thermal resistance, junction to heat sink	0.021	K/W	DC operation double side cooled
F	Mounting force, $\pm 10\%$	24500 (2500)	N (kg)	
w t	Approximate weight	425	g	
	Case style	A-24(K-PUK)		See outline

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2500PK .Series

Outline Table

